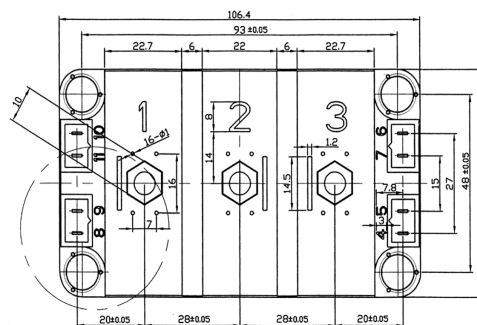
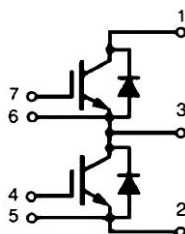
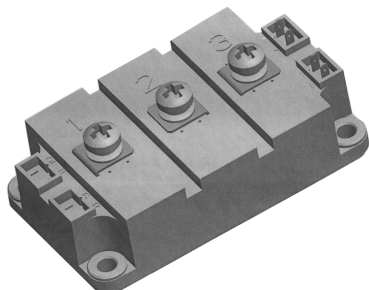


Dimensions in mm (1mm = 0.0394")



Absolute Maximum Ratings

$T_c = 25^{\circ}\text{C}$, unless otherwise specified

Symbol	Conditions	Values	Units
IGBT Wechselrichter/ IGBT Inverter			
V_{CES}		1200	V
I_c	$T_c = 25(80)^{\circ}\text{C}$, $T_{vj} = 150^{\circ}\text{C}$	625(300)	A
I_{CRM}	$T_c = 80^{\circ}\text{C}$, $t_P = 1\text{ms}$	600	A
P_{tot}	$T_c = 25^{\circ}\text{C}$, $T_{vj} = 150^{\circ}\text{C}$	2500	W
V_{GES}		± 20	V
Diode Wechselrichter/ Diode Inverter			
V_{RRM}		1200	V
I_F		300	A
I_{FRM}	$t_P = 1\text{ms}$	600	A
I_t^2	$V_R = 0\text{V}$, $t_P = 10\text{ms}$; $T_{vj} = 125^{\circ}\text{C}$	19000	A^2s
Module Isolation/ Module Isolation			
V_{ISOL}	RMS, $f = 50\text{Hz}$, $t = 1\text{min}$, NTC connect to Baseplate	2500	V

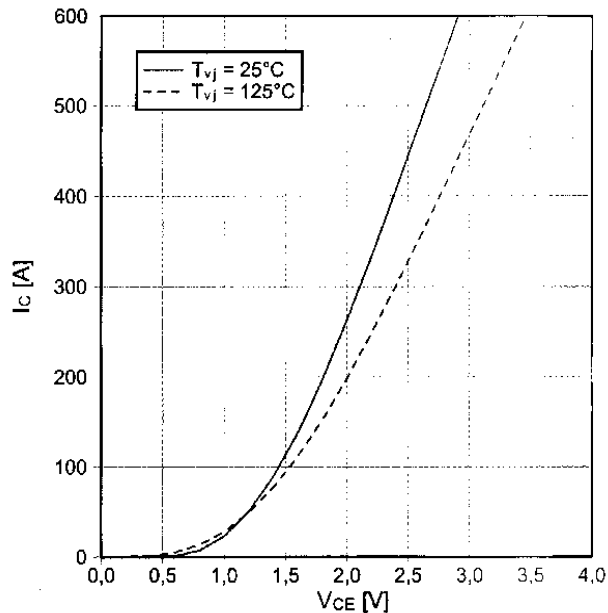
Characteristics

$T_c = 25^{\circ}\text{C}$, unless otherwise specified

Symbol	Conditions	min.	typ.	max.	Units
IGBT Wechselrichter/ IGBT Inverter					
V_{GEth}	$V_{GE} = V_{CE}$, $I_c = 12\text{mA}$	4.5	5.5	6.5	V
I_{CES}	$V_{GE} = 0$; $V_{CE} = 1200\text{V}$			5	mA
I_{GES}	$V_{CE}=0$; $V_{GE}=20\text{V}$			400	nA
R_{Gint}			1.0		Ω
$V_{CE(sat)}$	$I_c = 300\text{A}$; $V_{GE} = 15\text{V}$; $T_j = 25(125)^{\circ}\text{C}$		2.1(2.4)	2.6(2.9)	V
C_{ies}	under following conditions		21		nF
C_{res}	$V_{GE} = 0$, $V_{CE} = 25\text{V}$, $f = 1\text{MHz}$		1.4		
Q_G	$V_{GE} = -15\text{V} \dots +15\text{V}$		3.2		μC
I_{sc}	$t_P \leq 10\mu\text{s}$, $V_{GE} \leq 15\text{V}$, $T_{vj} = 125^{\circ}\text{C}$, $V_{CC} = 900\text{V}$		1800		A
$t_{d(on)}$	under following conditions: $V_{CE} = 600\text{V}$, $I_c = 300\text{A}$		110(120)		ns
t_r	$R_{Gon} = R_{Goff} = 3.3\Omega$, $T_j = 25(125)^{\circ}\text{C}$		60(70)		ns
$t_{d(off)}$	$V_{GE} = \pm 15\text{V}$		550(570)		ns
t_f			70(80)		ns
$E_{on}(E_{off})$	$T_j = 25(125)^{\circ}\text{C}$, $L_s = 60\text{nH}$		35(36)		mJ
R_{thJC}				0.05	K/W
R_{thCH}			0.03		
Diode Wechselrichter/ Diode Inverter					
V_F	under following condition $I_F = 300\text{A}$; $V_{GE} = 0\text{V}$; $T_j = 25(125)^{\circ}\text{C}$		1.8(1.7)	2.3(2.2)	V
I_{RM}	$I_F = 300\text{A}$; $T_j = 25(125)^{\circ}\text{C}$		350(420)		A
Q_r	$-di/dt = 5400\text{A}/\mu\text{s}$		28(58)		μC
E_{rec}	$V_{GE} = -15\text{V}$, $V_R = 600\text{V}$		9(21)		mJ
R_{thJC}				0.125	K/W
R_{thCH}			0.06		
Modul/ module					
R_{thCH}	under following conditions $I_c = 15\text{A}$; $V_{GE} = 15\text{V}$; $T_j = 25(125)^{\circ}\text{C}$		1.7(2.0)	2.15	V
L_{sCE}	$V_{CE}=V_{GE}$, $I_c=0.5\text{mA}$	5.0	5.8	6.5	V
$R_{CC'+EE'}$	$f=1\text{MHz}$, $V_{CE}=25\text{V}$, $V_{GE}=0\text{V}$		1.1		nF
T_{vj}			-40...+125		$^{\circ}\text{C}$
T_{vJM}			150		
T_{stg}			-40...+125		
Mechanical Data					
M_s	to heatsink M6	3		5	Nm
M_t	to terminals M5	2.5		5	Nm
W				325	g

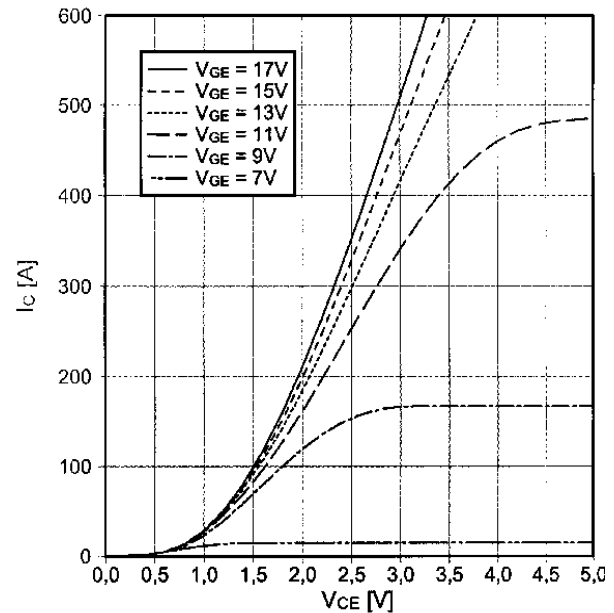
Ausgangskennlinie IGBT-Wechselr. (typisch)
output characteristic IGBT-inverter (typical)

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



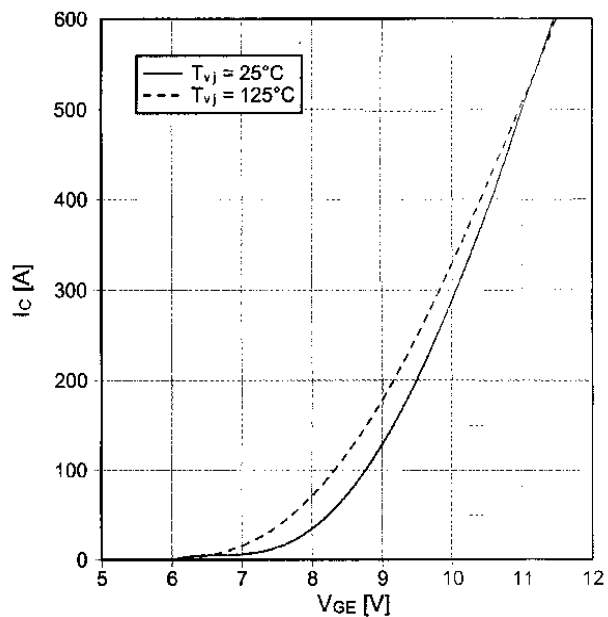
Ausgangskennlinienfeld IGBT-Wechselr. (typisch)
output characteristic IGBT-inverter (typical)

$I_C = f(V_{CE})$
 $T_{vj} = 125^\circ\text{C}$



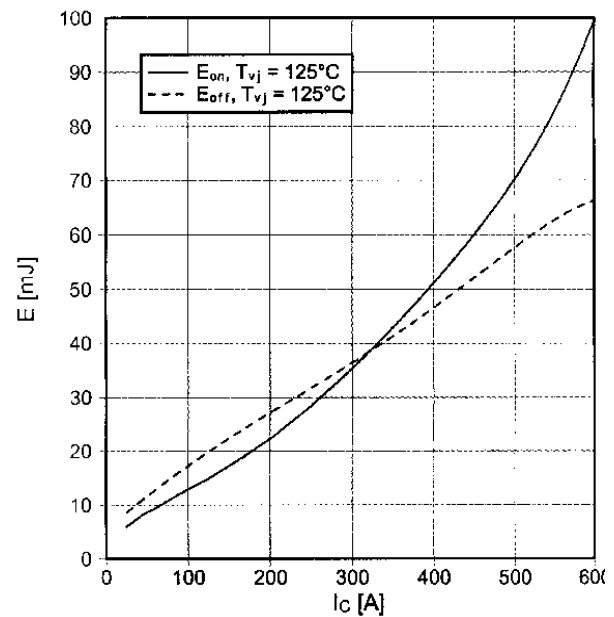
Übertragungscharakteristik IGBT-Wechselr. (typisch)
transfer characteristic IGBT-inverter (typical)

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$

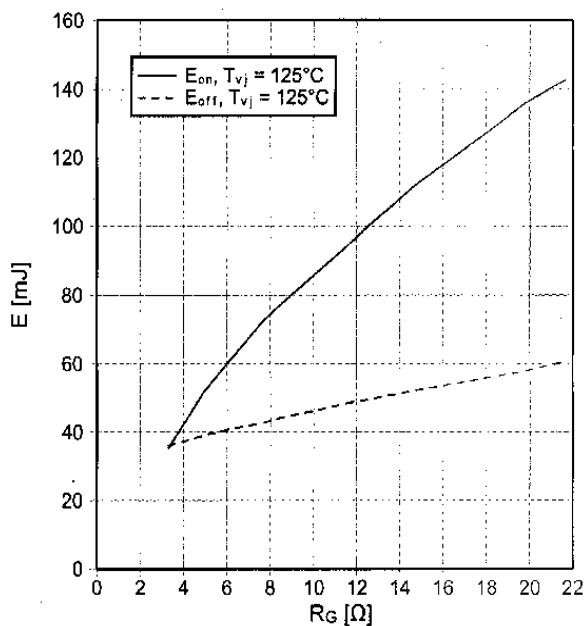


Schaltverluste IGBT-Wechselr. (typisch)
switching losses IGBT-inverter (typical)

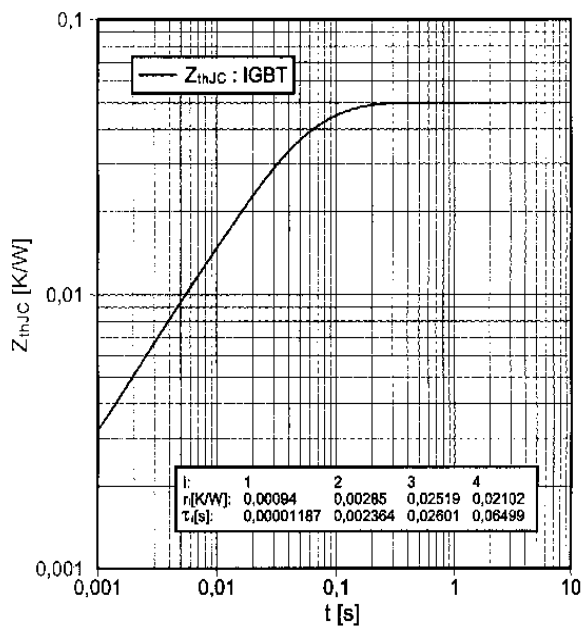
$E_{on} = f(I_C)$, $E_{off} = f(I_C)$
 $V_{GE} = \pm 15\text{ V}$, $R_{Gon} = 3,3\ \Omega$, $R_{Goff} = 3,3\ \Omega$, $V_{CE} = 600\text{ V}$



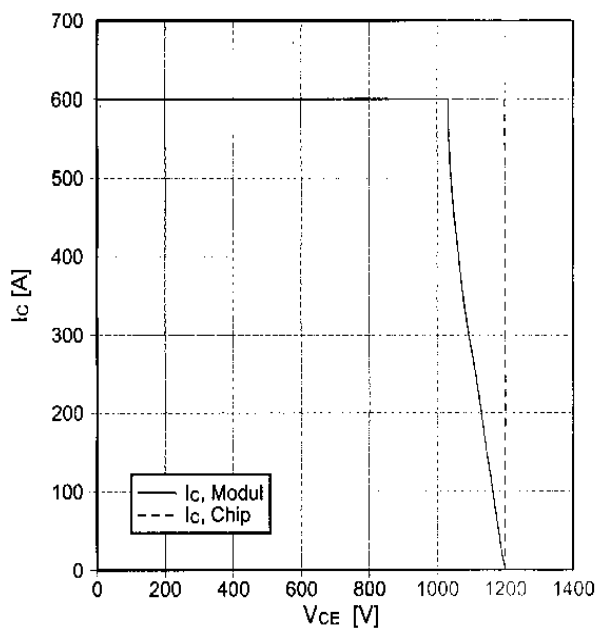
Schaltverluste IGBT-Wechselr. (typisch)
switching losses IGBT-Inverter (typical)
 $E_{on} = f(R_G)$, $E_{off} = f(R_G)$
 $V_{GE} = \pm 15 \text{ V}$, $I_C = 300 \text{ A}$, $V_{CE} = 600 \text{ V}$



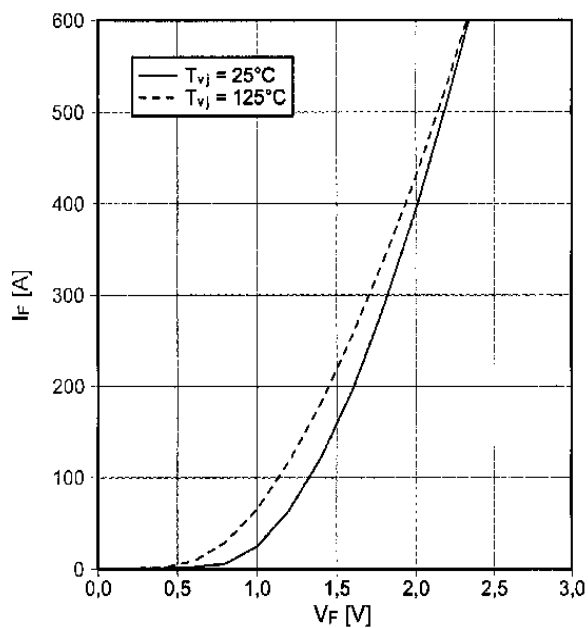
Transienter Wärmewiderstand IGBT-Wechselr.
transient thermal impedance IGBT-inverter
 $Z_{thJC} = f(t)$



Sicherer Rückwärts-Arbeitsbereich IGBT-Wr. (RBSOA)
reverse bias safe operating area IGBT-inv. (RBSOA)
 $I_C = f(V_{CE})$
 $V_{GE} = \pm 15 \text{ V}$, $R_{Goff} = 3,3 \Omega$, $T_{vj} = 125^\circ\text{C}$

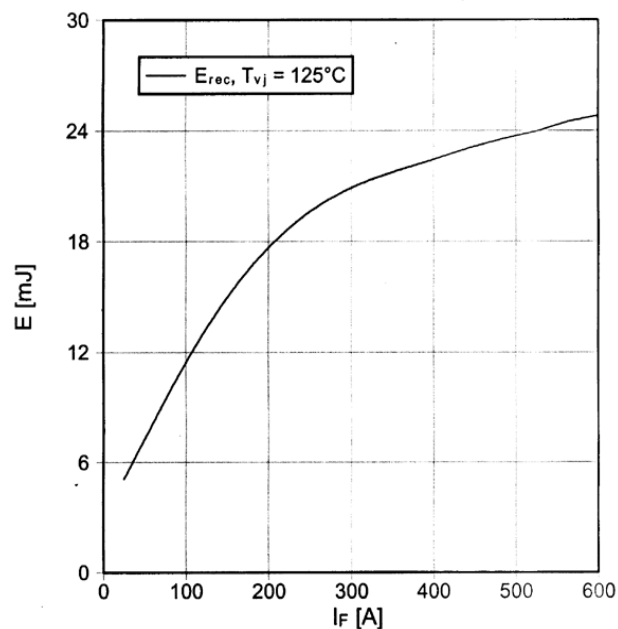


Durchlaßkennlinie der Diode-Wechselr. (typisch)
forward characteristic of diode-inverter (typical)
 $I_F = f(V_F)$



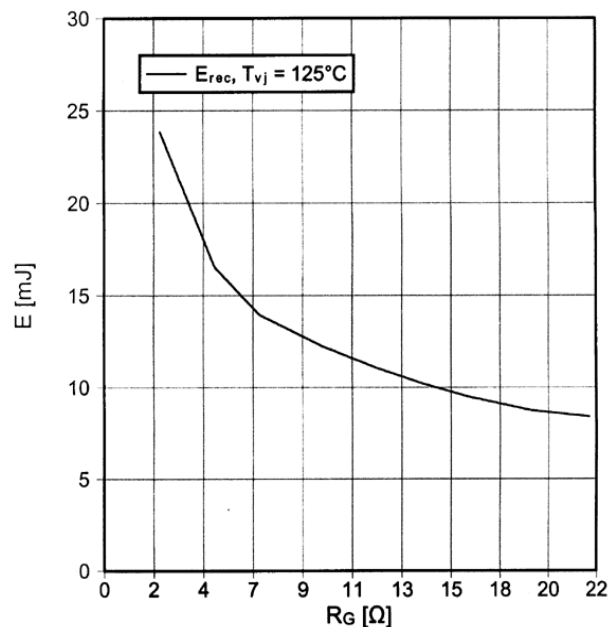
Schaltverluste Diode-Wechselr. (typisch)
switching losses diode-inverter (typical)

$E_{rec} = f(I_F)$
 $R_{Gon} = 3,3 \Omega$, $V_{CE} = 600 V$



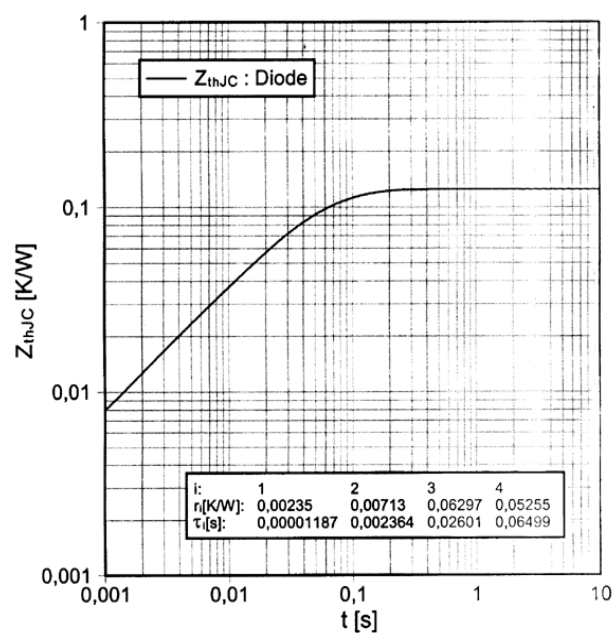
Schaltverluste Diode-Wechselr. (typisch)
switching losses diode-inverter (typical)

$E_{rec} = f(R_G)$
 $I_F = 300 A$, $V_{CE} = 600 V$



Transienter Wärmewiderstand Diode-Wechselr.
transient thermal impedance diode-inverter

$Z_{thJC} = f(t)$



i:	1	2	3	4
η [K/W]:	0,00235	0,00713	0,06297	0,05255
τ [s]:	0,00001187	0,002364	0,02601	0,06499